

Yahor Lebiadok

List of Publications by Year in descending order

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20
papers

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citations

1478505

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21
all docs

21
docs citations

21
times ranked

84
citing authors

#	ARTICLE	IF	CITATIONS
1	Diffusion in GaN/AlN superlattices: DFT and EXAFS study. Applied Surface Science, 2020, 515, 146001.	6.1	20
2	Graphene-like Si ₃ N ₃ and Si ₃ N ₄ Nanolayers on Silicon Surface. , 2019, , .		0
3	Structure and Charge of Nitrogen and Gallium Vacancies Located in the AlN/GaN Interface of Quantum Wells. , 2018, , .		0
4	GaInAsSb-based lasers for environmental monitoring. , 2018, , .		0
5	Auger Recombination and Amplified Luminescence in InAsSb/InAsSbP LEDs at 10 ^{−60} K. Journal of Applied Spectroscopy, 2017, 84, 843-849.	0.7	5
6	Compact Diode-Side-Pumped Stimulated Raman Laser Based on a KGW:Nd Crystal. Journal of Applied Spectroscopy, 2015, 82, 483-486.	0.7	0
7	Light emitting diode-photodiode optoelectronic pairs based on the InAs/InAsSb/InAsSbP heterostructure for the detection of carbon dioxide. Semiconductors, 2015, 49, 980-983.	0.5	6
8	Amplified Luminescence and Parasitic Laser Modes in the Active Medium of a Transverse Diode-Pumped Nd:YAG Laser. Journal of Applied Spectroscopy, 2015, 82, 573-577.	0.7	2
9	Efficiency of laser-diode-array side pumping of a passively Q-switched erbium laser. Journal of Optical Technology (A Translation of Opticheskii Zhurnal), 2015, 82, 576.	0.4	1
10	Point defects and amplification in active layers of InGaAs/AlGaAs heterostructures. Physics of the Solid State, 2013, 55, 2165-2168.	0.6	3
11	Transversally diode-pumped Q-switched Nd:YAG laser with improved power and spatial characteristics. Optics Communications, 2013, 308, 26-29.	2.1	14
12	Optimal output mirror reflection coefficient for powerful InGaAs/AlGaAs laser diode arrays. Optics and Laser Technology, 2013, 45, 177-180.	4.6	4
13	Optimized diode-pumped passive Q-switched ytterbium-erbium glass laser. Applied Physics B: Lasers and Optics, 2012, 108, 283-288.	2.2	6
14	Radiative and nonradiative recombination in the active layers of high-power InGaAs/GaAs/AlGaAs laser diodes. Semiconductors, 2012, 46, 1316-1320.	0.5	7
15	Amplified luminescence in InGaAs/AlGaAs laser diode arrays at high pump levels. Journal of Applied Spectroscopy, 2012, 78, 811-816.	0.7	2
16	Optimal fill factor for laser diode arrays applied to transversally pumped erbium laser. Optics Communications, 2012, 285, 2397-2401.	2.1	4
17	Loss coefficient for amplified luminescence of laser diode arrays. Journal of Applied Spectroscopy, 2011, 77, 810-816.	0.7	3
18	Amplified luminescence and output characteristics of high-power InGaAs/AlGaAs laser diode arrays. Quantum Electronics, 2011, 41, 95-98.	1.0	6

#	ARTICLE	IF	CITATIONS
19	The temperature dependence of internal parameters of disc laser diodes InAs/InAsSbP. Semiconductors, 2009, 43, 500-504.	0.5	3
20	Interband transition matrix element and temperature dependence of the lasing threshold for GaN laser structures. Journal of Applied Spectroscopy, 2007, 74, 878-883.	0.7	6